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(54) **NAND STAIRCASE LANDING PADS
CONVERSION**

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ABSTRACT

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Methods, systems, and devices for NAND staircase landing pads conversion are described. A memory device may include one or more lateral word line contacts that may couple a word line with a conductive pillar that traverses a stack of materials of the memory device. The use of the lateral word line contact may allow for a conductive pillar to be coupled with a target word line without requiring an end of the conductive pillar to be placed directly on the word line. Additionally, the memory architecture described herein may allow for the target word line to be coupled with CMOS circuitry via a first conductive pillar without the use of a second conductive pillar, as the first conductive pillar may traverse the stack of materials and be coupled with the CMOS circuitry. Therefore, total quantity of conductive pillars may be reduced, and the risk of manufacturing errors may be lowered.

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